PRELIMINARY

Notice : This is not a final specification
Some parametric are subject to change.

INJ0203CC1

High Speed Switching
Silicon P-channel MOSFET

DESCRIPTION

INJ0203CC1 is a Silicon P-channel MOSFET.
This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

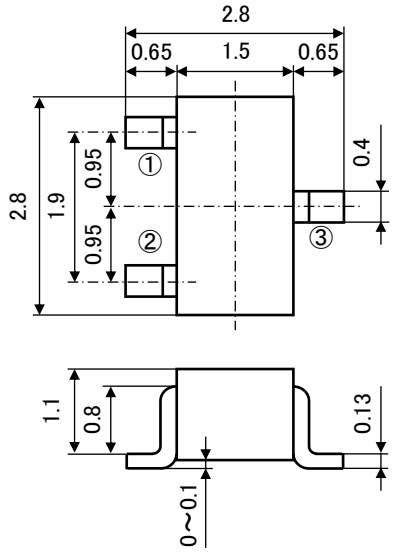
・Input impedance is high, and not necessary to consider a drive electric current.
・High drain current ID=−2.6A
・Drive voltage −2.5V
・Low on Resistance. RDS(ON)=100mΩtyp(@VGS=−4.5V)
RDS(ON)=220mΩtyp(@VGS=−2.5V)
・High speed switching.

APPLICATION

High speed switching, Analog switching

OUTLINE DRAWING

Unit : mm



TERMINAL CONNECTOR

①:GATE
②:SOURCE
③:DRAIN

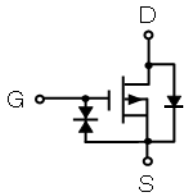
JEITA:SC-59
JEDEC:Similar to TO-236

MAXIMUM RATINGS (Ta=25℃)

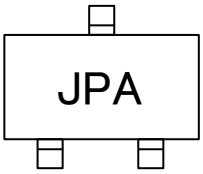
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	−20	V
Gate-Source Voltage	V_{GSS}	±10	V
Drain Current(DC) (※1)	I_D	−2.6	A
Drain Current(Pulse) (※2)	I_{DP}	−10	A
Total Power Dissipation (※1)	P_D	0.9	W
Channel Temperature	T_{ch}	+150	℃
Storage Temperature	T_{stg}	−55～+150	℃

※1 package mounted on glass-epoxy substrate.
(39mm×39mm×1.6mm)
※2 Pw≦1ms , Duty cycle≦1%

EQUIVALENT CIRCUIT



MARKING

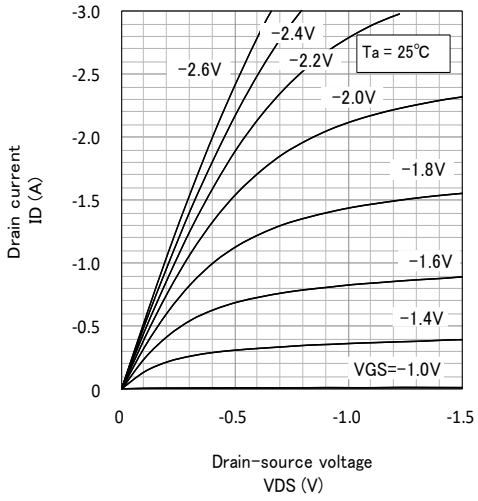


ELECTRICAL CHARACTERISTICS (Ta=25℃)

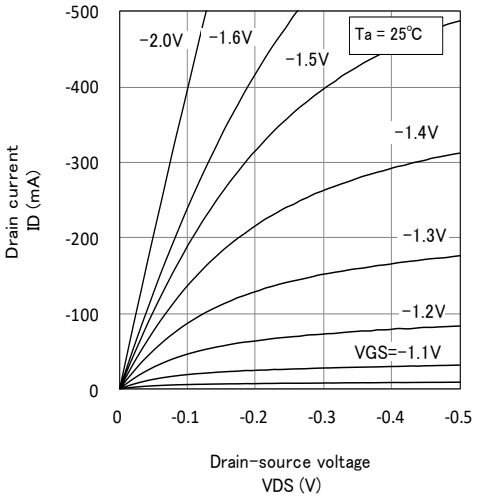
Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−100μA, V_{GS}=0V	−20	−	−	V
Gate-Source Leak Current	I_{GSS}	V_{GS}=±10V, V_{DS}=0V	−	−	±10	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=−20V, V_{GS}=0V	−	−	−1.0	μA
Gate Threshold Voltage	V_{th}	I_D=−250μA, V_{DS}= V_{GS}	−0.4	−	−1.2	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	I_D=−2.6A, V_{GS}=−4.5V	−	100	150	mΩ
		I_D=−2.6A, V_{GS}=−2.5V	−	220	290	
Input Capacitance	C_{iss}	V_{DS}=−10V, V_{GS}=0V, f=1MHz	−	320	−	pF
Output Capacitance	C_{oss}		−	90	−	
Feedback Capacitance	C_{rss}		−	90	−	
Switching Time	t_{on}	V_{DD}=−20V, I_D=−200mA, V_{GS}=−5V	−	320	−	ns
	t_{off}		−	1900	−	

TYPICAL CHARACTERISTICS

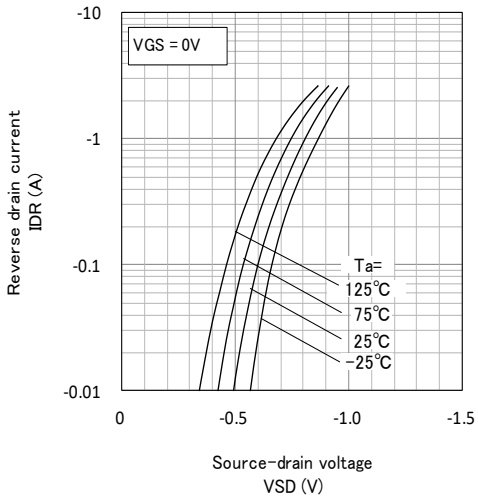
ID - VDS



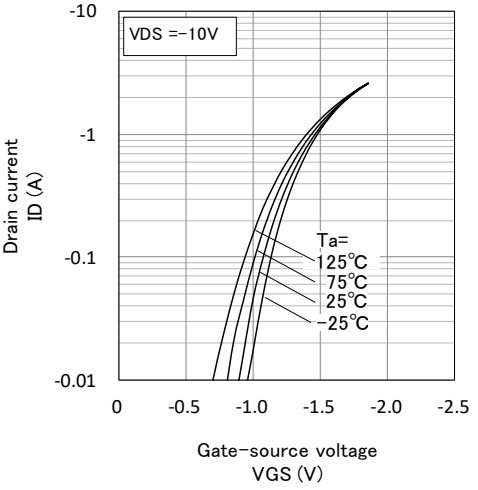
ID - VDS(Low Voltage Region)



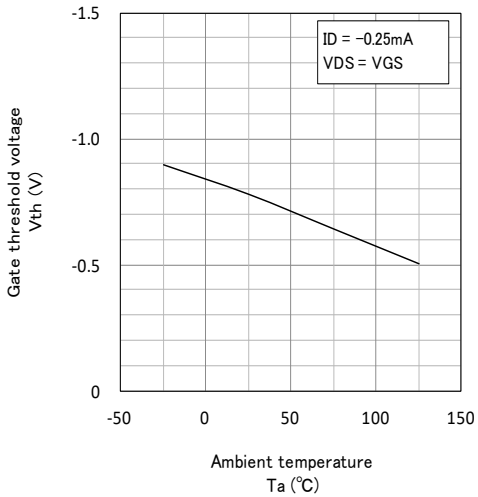
IDR - VSD



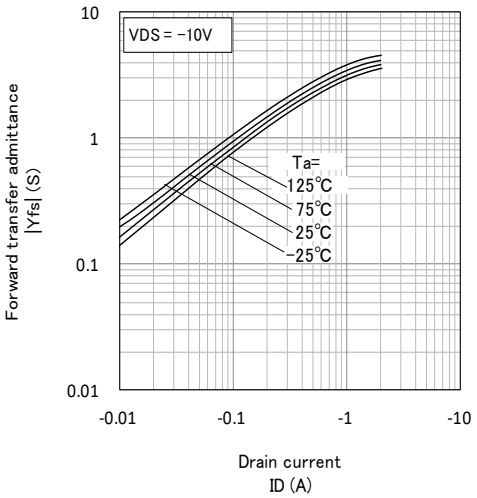
ID - VGS



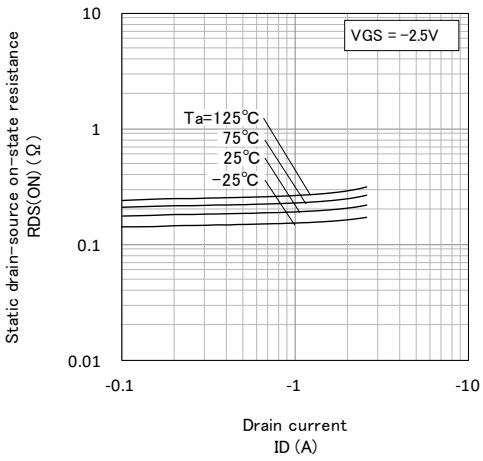
Vth - Ta



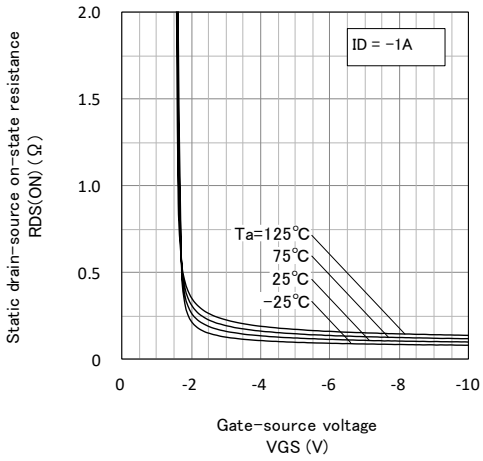
|Yfs| - ID



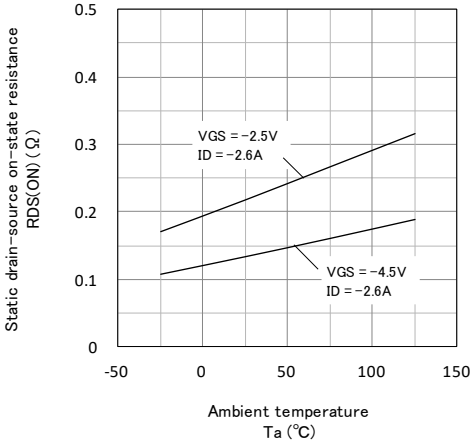
RDS(ON) – ID



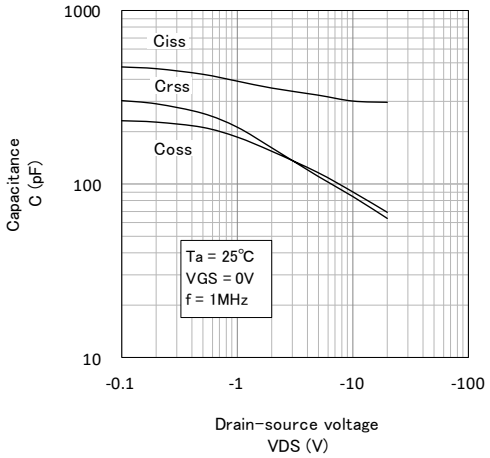
RDS(ON) – VGS



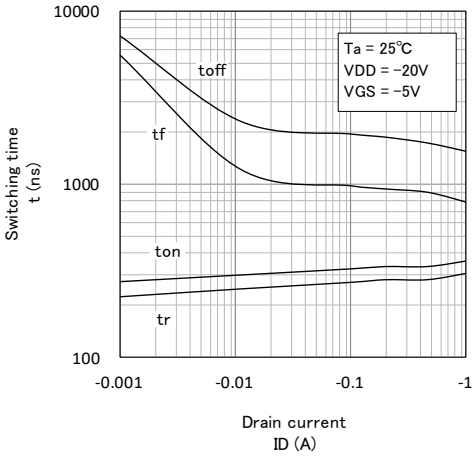
RDS(ON) – Ta



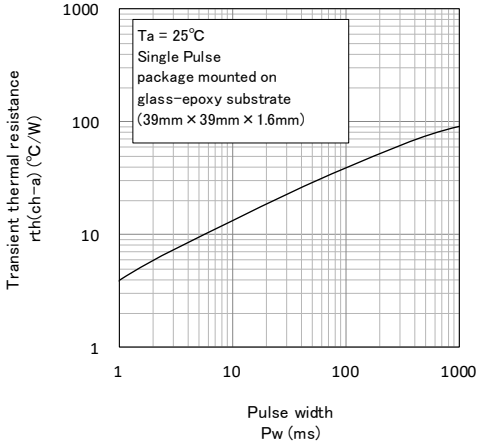
C – VDS



t – ID



rth(ch-a) – Pw



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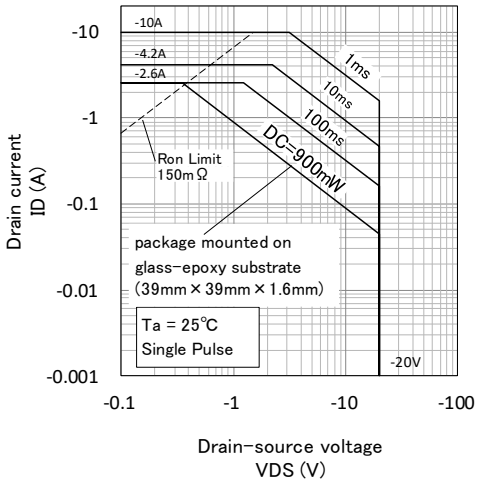
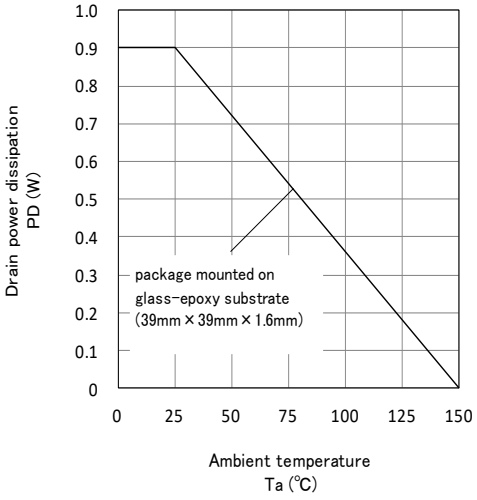
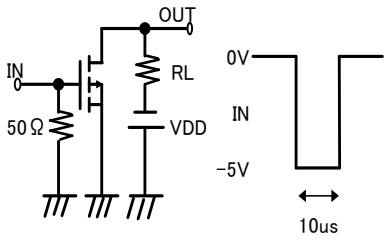
ASO



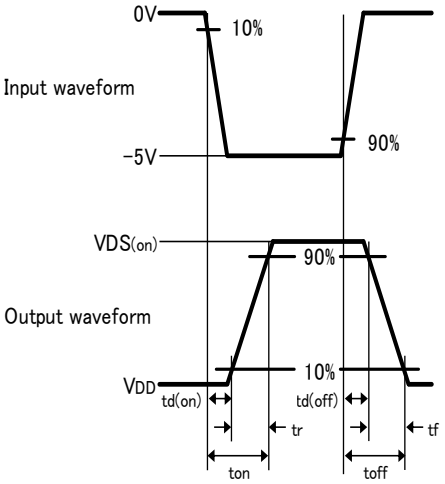
PD - Ta



Switching time test condition



Duty ≦ 1%
Input : tr, tf < 10ns
VDD = −20V
Common source
Ta = 25℃



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